



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	<b>Atty Docket No.</b>	NOVLP094/NVLS-2919
	<b>Application No.:</b>	10/789,103
	<b>Applicant</b>	Wu et al.
	<b>Filing Date</b>	February 27, 2004
	<b>Group</b>	1762
		Page 1 of 1

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	1.	7,166,531	01.2007	van den Hoek et al.			
	2.	7,176,144	02.2007	Wang et al.			
	3.	6,268,288 B1	07.2001	Hautala et al.			
	4.	6,759,098 B2	07.2004	Han et al.			
	5.	6,576,300 B1	06.2003	Berry et al.			
	6.	6,558,755 B2	05.2003	Berry et al.			
	7.	2002/0172766 A1	11.2002	Laxman et al.			
	8.	6,479,409 B2	11.2002	Shioya et al.			
	9.	6,921,727 B2	07.2005	Chiang et al.			
	10.	6,740,602 B1	05.2004	Hendriks et al.			
	11.	2005/0156285 A1	07.2005	Gates et al.			
	12.	7,064,088 B2	06.2006	Hyodo et al.			
	13.	7,241,704 B1	07.10.07	Wu et al.			

#### Other Documents

Examiner Initial	No.	Author, Title, Place (e.g. Journal) of Publication, Date
	14.	U.S. Office Action dated November 28, 2007, from U.S. Application No. 10/807,680 [Atty Dkt: NOVLP97/NVLS-2906]
	15.	R.J. Lewis, Sr., Hawley's Condensed Chemical Dictionary, 12 <sup>th</sup> Edition, Van Nostrand Reinhold Co., New York, 1993 (no month), excerpts pages 916-918 & 1123-1124.
	16.	Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 11/764,750, filed June 18, 2007 [Atty Dkt: NOVLP106D1/NVLS-2930D1]
	17.	Wu et al., "Methods For Producing Low-K CDO Films," U.S. Application No. 11/936,754, filed November 7, 2007 [Atty Docket No.: NOVLP098D1/NVLS-2907D1]
	18.	Wu et al., "Methods For Improving Integration Performance of Low Stress CDO Films", U.S. Application No. 11/936,752, filed November 7, 2007 [Atty Dkt: NOVLP107D1/NVLS-2932D1]
	19.	U.S. Notice of Allowance and Fee Due mailed September 27, 2007, from U.S. Application No. 11/376,510. [NOVLP099D1/NVLS-2896D1]
	20.	Allowed Claims from U.S. Application No. 11/376,510. [NOVLP099D1/NVLS-2896D1]

<b>Examiner</b>	<b>Date Considered</b>
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.